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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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MITSUBISHI IGBT MODULES
CM150RL-24NF

HIGH POWER SWITCHING USE

CM150RL-24NF



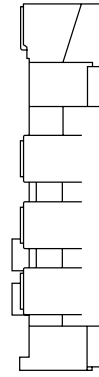
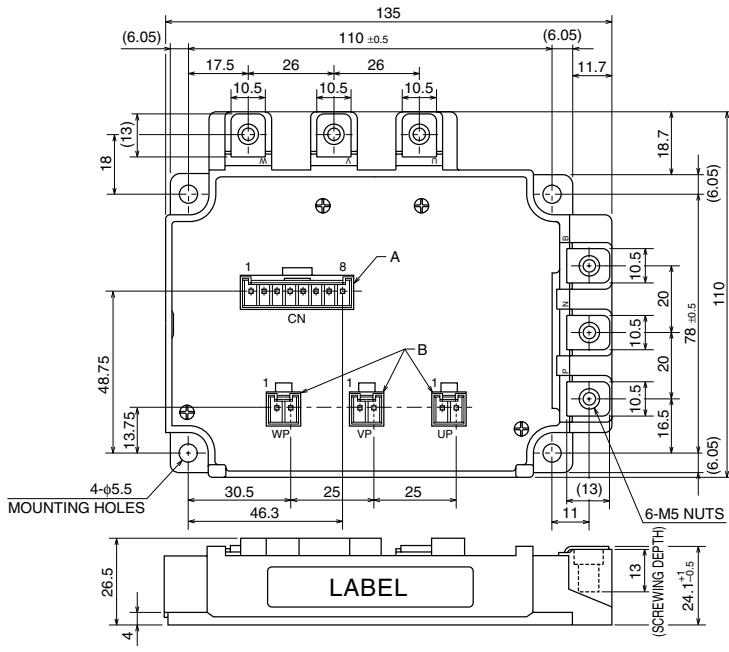
- IC 150A
- VCES 1200V
- Insulated Type
- 7-elements in a pack

APPLICATION

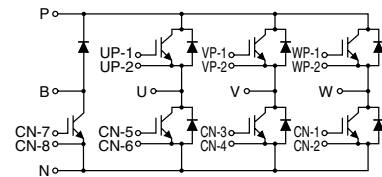
AC drive inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Housing Type of A and B
 (J.S.T.Mfg.Co.Ltd)
 A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

CM150RL-24NF

HIGH POWER SWITCHING USE

ABSOLUTE MAXIMUM RATINGS (T_j = 25°C, unless otherwise specified)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	1200	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	DC, T _c = 76°C*1	150	A
I _{CM}		Pulse (Note 2)	300	A
I _E (Note 1)	Emitter current		150	A
I _{EM} (Note 1)		Pulse (Note 2)	300	A
P _C (Note 3)	Maximum collector dissipation	T _c = 25°C	890	W

BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	1200	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	DC, T _c = 86°C*1	75	A
I _{CM}		Pulse (Note 2)	150	A
P _C (Note 3)	Maximum collector dissipation	T _c = 25°C	520	W
V _{RRM}	Repetitive peak reverse voltage	Clamp diode part	1200	V
I _{FM}	Forward current	Clamp diode part	75	A

(COMMON RATING)

Symbol	Parameter	Conditions	Ratings	Unit
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
V _{iso}	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute	2500	V _{rms}
—	Torque strength	Main terminals M5 screw	2.5 ~ 3.5	N • m
—		Mounting M5 screw	2.5 ~ 3.5	N • m
—	Weight	Typical value	750	g

CM150RL-24NF

HIGH POWER SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

INVERTER PART

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA	
VGE(th)	Gate-emitter threshold voltage	IC = 15mA, VCE = 10V	6	7	8	V	
IGES	Gate leakage current	±VGE = VGES, VCE = 0V	—	—	0.5	μA	
VCE(sat)	Collector-emitter saturation voltage	IC = 150A, VGE = 15V	T _j = 25°C	—	2.1	3.0	V
			T _j = 125°C	—	2.4	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	23	nF	
Coes	Output capacitance		—	—	2	nF	
Cres	Reverse transfer capacitance		—	—	0.45	nF	
QG	Total gate charge	VCC = 600V, IC = 150A, VGE = 15V	—	675	—	nC	
td(on)	Turn-on delay time	VCC = 600V, IC = 150A VGE = ±15V RG = 2.1Ω, Inductive load IE = 150A	—	—	130	ns	
tr	Turn-on rise time		—	—	70	ns	
td(off)	Turn-off delay time		—	—	400	ns	
tf	Turn-off fall time		—	—	350	ns	
trr (Note 1)	Reverse recovery time		—	—	150	ns	
Qrr (Note 1)	Reverse recovery charge	—	5.8	—	μC		
VEC(Note 1)	Emitter-collector voltage	IE = 150A, VGE = 0V	—	—	3.8	V	
Rth(j-c)Q	Thermal resistance	IGBT part (1/6 module) ^{*1}	—	—	0.14	K/W	
Rth(j-c)R		FWDi part (1/6 module) ^{*1}	—	—	0.23	K/W	
Rth(c-f)	Contact thermal resistance	Case to heat sink, Thermal compound Applied (1/6 module) ^{*2}	—	0.051	—	K/W	
RG	External gate resistance		2.1	—	31	Ω	

BRAKE PART

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA	
VGE(th)	Gate-emitter threshold voltage	IC = 7.5mA, VCE = 10V	6	7	8	V	
IGES	Gate leakage current	±VGE = VGES, VCE = 0V	—	—	0.5	μA	
VCE(sat)	Collector-emitter saturation voltage	IC = 75A, VGE = 15V	T _j = 25°C	—	2.1	3.0	V
			T _j = 125°C	—	2.4	—	
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	11.5	nF	
Coes	Output capacitance		—	—	1.0	nF	
Cres	Reverse transfer capacitance		—	—	0.23	nF	
QG	Total gate charge	VCC = 600V, IC = 75A, VGE = 15V	—	338	—	nC	
VFM	Forward voltage drop	IF = 75A	—	—	3.8	V	
Rth(j-c)Q	Thermal resistance	IGBT part ^{*1}	—	—	0.24	K/W	
Rth(j-c)R		Clamp diode part ^{*1}	—	—	0.36	K/W	
RG	External gate resistance		4.2	—	42	Ω	

*1 : Case temperature (T_c) measured point is just under the chips.

If you use this value, Rth(f-a) should be measured just under the chips.

*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

Note 1. IE, VEC, trr & Qrr represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

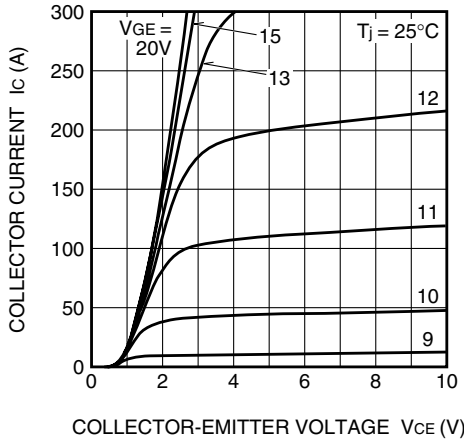
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

CM150RL-24NF

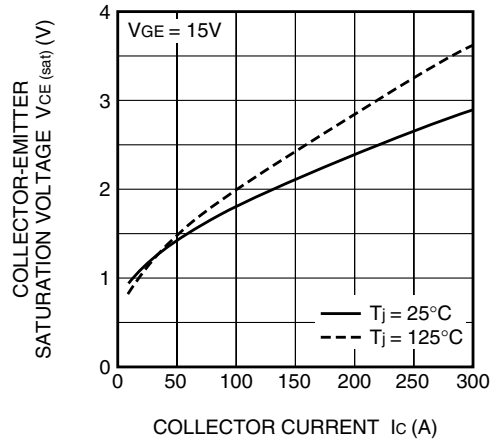
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

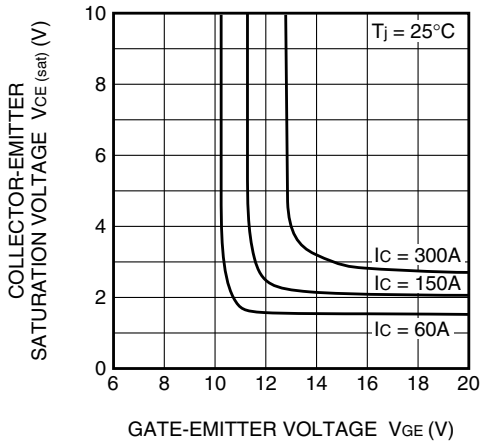
OUTPUT CHARACTERISTICS (TYPICAL)



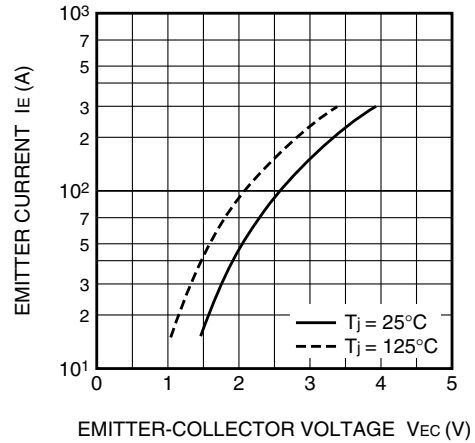
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



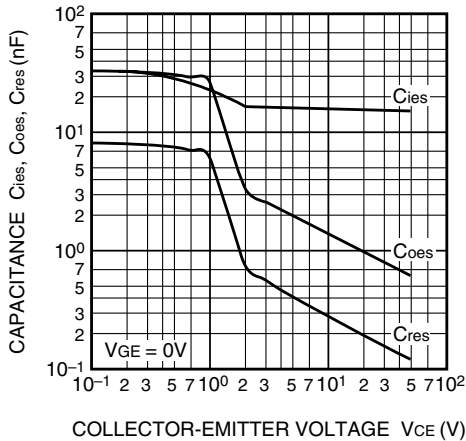
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



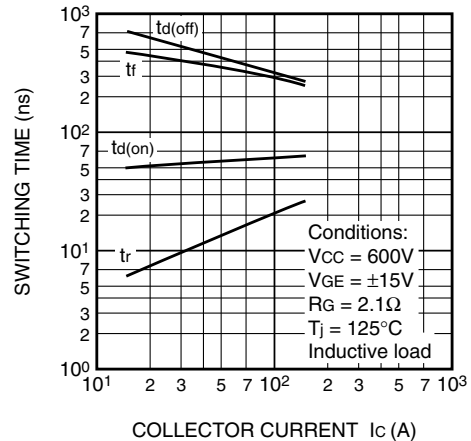
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)



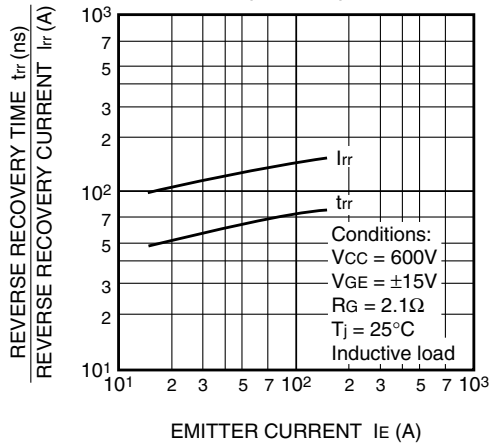
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



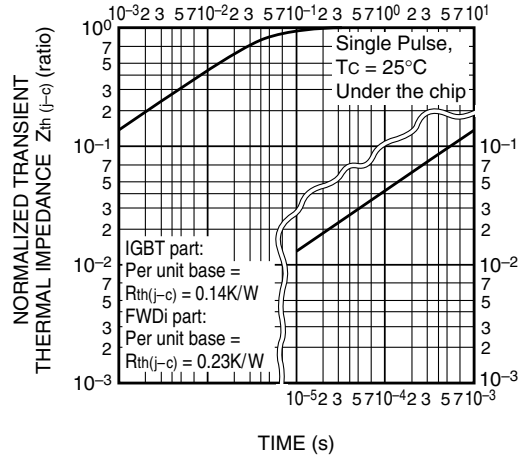
CM150RL-24NF

HIGH POWER SWITCHING USE

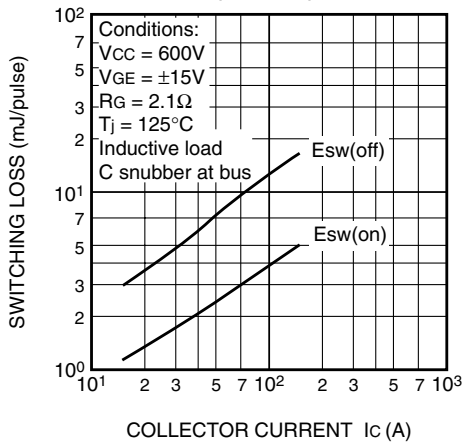
REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



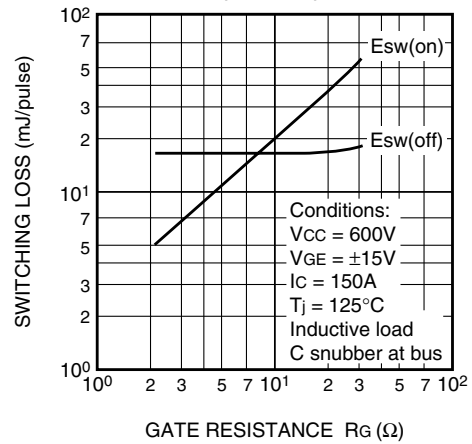
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



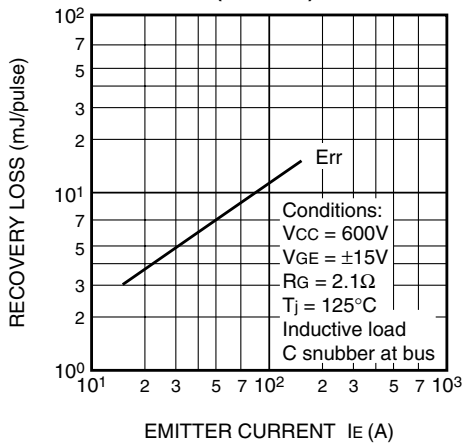
SWITCHING LOSS vs. COLLECTOR CURRENT (TYPICAL)



SWITCHING LOSS vs. GATE RESISTANCE (TYPICAL)



RECOVERY LOSS vs. IE (TYPICAL)



RECOVERY LOSS vs. GATE RESISTANCE (TYPICAL)

